Analog Circuit Design (ACD) – ECE520

Home Assignment - 6

Total Marks: 10

Submission Deadline: 16.11.2013

Instructions:

- Answer all the questions.
- Please adhere to institute's plagiarism policy.
- Submit before 5:00pm on the submission day. No late submission allowed.

Q1. [4 marks] In the following circuit assume that: $\lambda_{\text{NFET}} = \lambda_{\text{PFET}} = 0$, and $\Upsilon = 0$, $V_{\text{DD}} = 1.8$ V, $I_{\text{bias}} = 50\mu$ A, $V_{\text{TN}} = |V_{\text{TP}}| = 0.4$ V, $\mu_{n}C_{\text{ox}} = 1$ mA/V², $\mu_{p}C_{\text{ox}} = 0.5$ mA/V².

Furthermore, assume that:

 $(W/L)_0 = (W/L)_1 = (W/L)_2 = (W/L)_3 = 10$ $(W/L)_4 = (W/L)_5 = (W/L)_6 = (W/L)_8 = (W/L)_9 = 20$ $(W/L)_7 = 5$, and $(W/L)_{10} = 60$.

Given that the dc level of the inputs (i.e., input common mode) is 1.2V:

- (a) Find the maximum and minimum voltage of V_{out1} and V_{out2} for which all the devices stay in saturation.
- (b) What is the differential output voltage swing?
- (c) Assuming that the circuit is driven by a differential signal, find the magnitude of the differential gain of the circuit, when a resistor of value 10 k Ω is connected between V_{out1} and V_{out2}.



Q2. [4 marks] For the following circuit, assume that at the frequencies of interest all the device parasitic capacitances can be ignored. Also, assume:

 $\lambda_{\text{NFET}} = \lambda_{\text{PFET}} = 0$, and $\Upsilon = 0$, $V_{\text{DD}} = 1.8$ V, $I_{\text{bias}} = 50\mu\text{A}$, $V_{\text{TN}} = |V_{\text{TP}}| = 0.4$ V, $\mu_{n}C_{\text{ox}} = 1$ mA/V², $\mu_{p}C_{\text{ox}} = 0.5$ mA/V², (W/L)₀ = 32, (W/L)₁ = 16, (W/L)₂ = 16, (W/L)₃ = 32, R_D = 1 k\Omega, $V_{\text{bias1}} = 0.65$ V, and $V_{\text{bias3}} = 1.15$ V.



(a) Find the minimum required V_{bias2} .

(b) What is the small-signal voltage gain of the circuit?

(c) Calculate (low frequency) input and output impedance of the circuit.

Q3. [2 marks] Calculate the gain of the following circuit (i.e., provide an expression of the gain in terms of circuit parameters):

(a) at very low frequencies

(b) at very high frequencies.

In this problem, neglect all other capacitances that are not shown in the circuit and assume $\Upsilon = \mathbf{0}$ for all three transistors, while $\lambda_0 = \lambda_1 = 0$ and $\lambda_2 \neq 0$.

